1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT60415PY

2. Features and benefits

- · High thermal power dissipation capability
- · High temperature applications up to 175 °C
- · Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- · Backlighting applications
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	40	V
I _C	collector current		-	-	15	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	30	А
R _{CEsat}	collector-emitter saturation resistance	I_C = 15 A; I_B = 1.5 A; $t_p \le 300 \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	28	40	mΩ



40 V, 15 A NPN high power bipolar transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	С
2	Е	emitter	<u> </u>	
3	Е	emitter	a	В —
4	В	base	0 0 0 0	Ė
mb	С	collector	1 2 3 4	sym123
			LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PHPT60415NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60415NY	0415NAB

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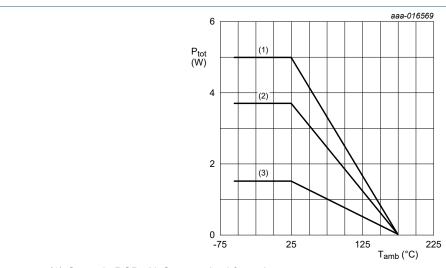
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	40	V
V _{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
Ic	collector current			-	15	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	30	Α
I _B	base current			-	1.5	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	3	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃, standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

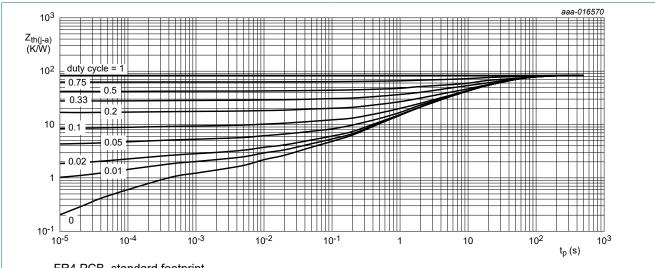
40 V, 15 A NPN high power bipolar transistor

9. Thermal characteristics

Table 6. Thermal characteristics

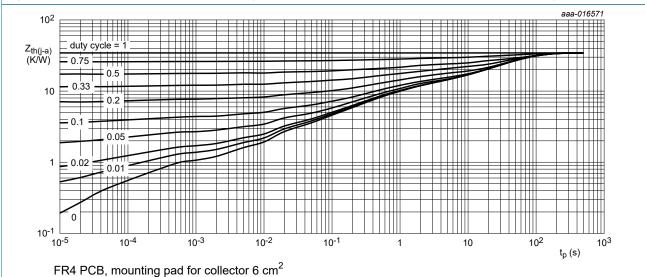
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from		[1]	-	-	100	K/W
	junction to ambient		[2]	-	-	41	K/W
			[3]	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

40 V, 15 A NPN high power bipolar transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 32 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 32 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 32 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 500 mA; T_{amb} = 25 °C	250	410	-	
		V_{CE} = 2 V; I_{C} = 1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	400	-	
		V_{CE} = 2 V; I_{C} = 10 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	160	-	
		V_{CE} = 2 V; I_{C} = 15 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	50	80	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_{amb} = 25 °C; pulsed	-	28	40	mV
		I_C = 10 A; I_B = 1 A; $t_p \le 300$ μs; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	250	400	mV
		$I_C = 15 \text{ A}; I_B = 1.5 \text{ A}; t_p \le 300 \mu\text{s};$	-	420	600	mV
R _{CEsat}	collector-emitter saturation resistance	pulsed; δ ≤ 0.02; T _{amb} = 25 °C	-	28	40	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1	V
		I_C = 10 A; I_B = 1 A; $t_p \le 300$ μs; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.35	V
		I_C = 15 A; I_B = 1.5 A; $t_p \le 300 \mu s$; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.5	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 500 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	0.8	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 8 A; I _{Bon} = 250 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = -250 mA; T _{amb} = 25 °C	-	215	-	ns
t _{on}	turn-on time		-	235	-	ns
t _s	storage time		-	290	-	ns
t _f	fall time		-	125	-	ns
t _{off}	turn-off time		-	415	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 500 mA; f = 100 MHz; T_{amb} = 25 °C	-	105	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	90	-	pF

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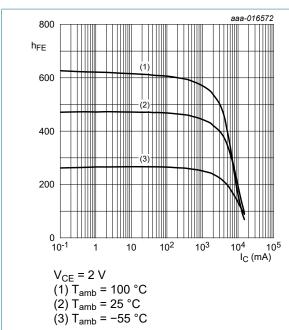


Fig. 4. DC current gain as a function of collector

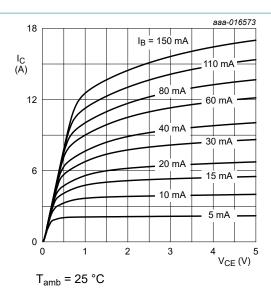
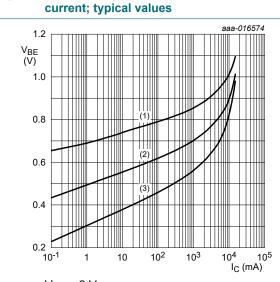
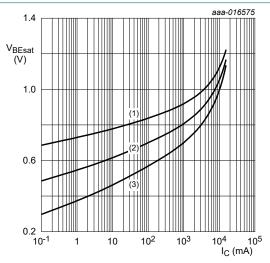


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $V_{CE} = 2 V$ (1) $T_{amb} = -55$ °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $I_C/I_B = 20$ (1) $T_{amb} = -55$ °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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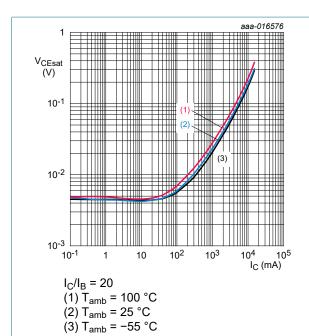


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

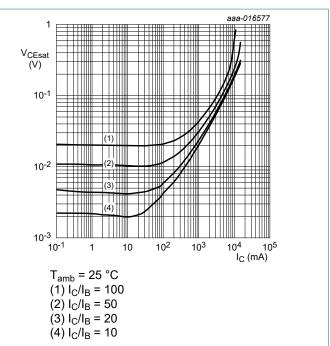
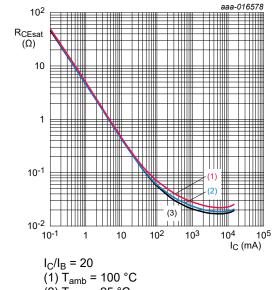
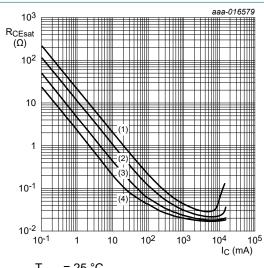


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



(1) $T_{amb} = 100 ^{\circ}C$ (2) $T_{amb} = 25 ^{\circ}C$ (3) $T_{amb} = -55 ^{\circ}C$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

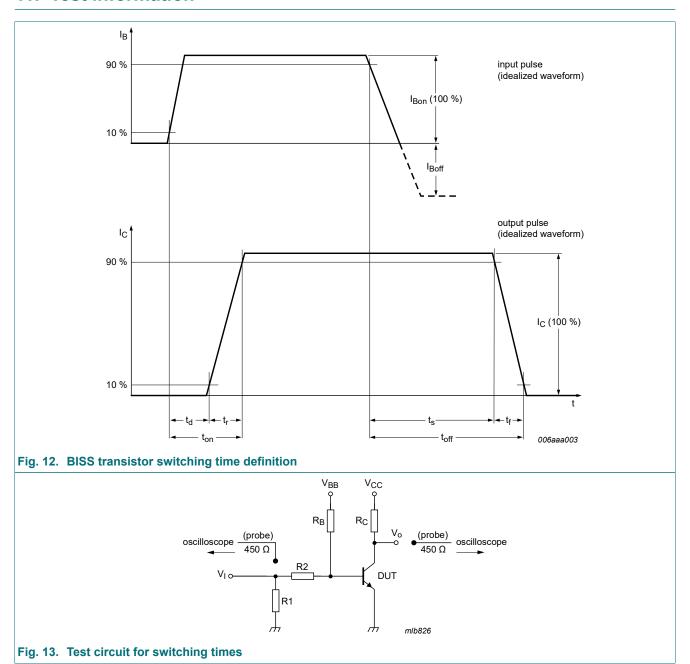


 $T_{amb} = 25 \,^{\circ}C$ (1) $I_C/I_B = 100$ (2) $I_C/I_B = 50$ (3) $I_C/I_B = 20$ (4) $I_C/I_B = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

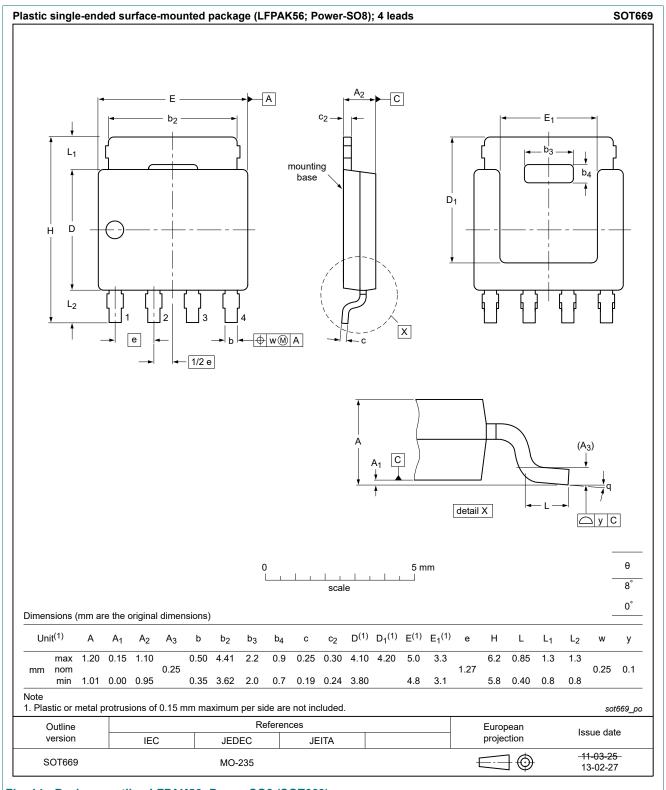
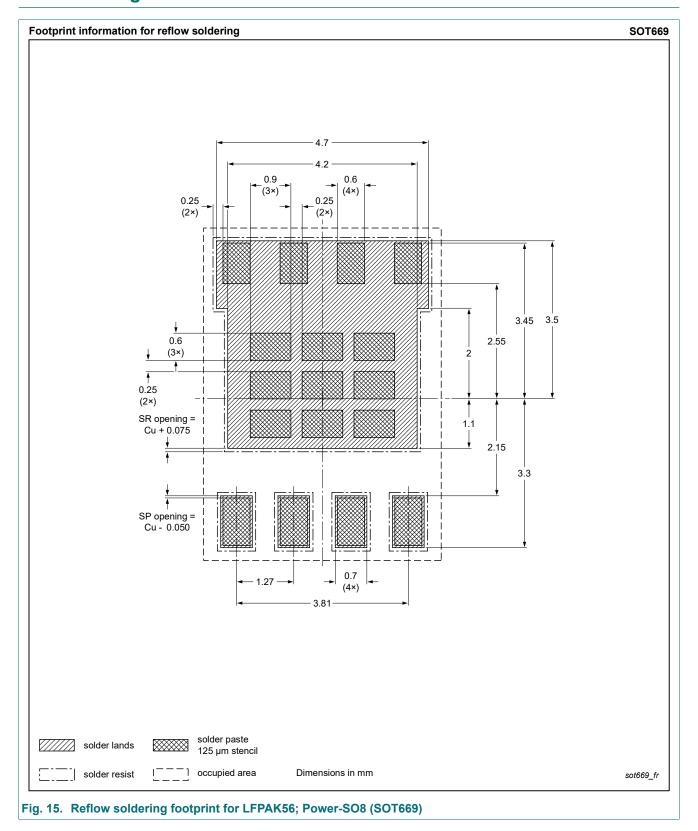


Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PHPT60415NY v.2	20190115	Product data sheet	-	PHPT60415NY v.1			
Modifications:	Typo at figures 2 and 3: unit corrected from ns to s at x-scale						
PHPT60415NY v.1	20150527	Product data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PHPT60415NY

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